

## MODULATOR

# NIR-MPX950-LN Series

## 950 nm band Phase Modulators

The Exail NIR-MPX950 series are phase modulators especially designed to operate in the 950 nm wavelength band. They are available with various modulation bandwidth, from low frequency to 20 GHz and beyond.

Like all Exail Near InfraRed (NIR) modulators, the NIR-MPX950 series use a proton exchanged based waveguide process that confers them an unparalleled stability and a high photo-refractive threshold.



### Features

- High optical power handling
- Wide bandwidth
- High stability
- Low  $V_{\pi}$
- Low insertion loss

### Applications

- Beam Combining
- Interferometric based sensors
- Quantum optics
- Frequency shifting
- Pound-Drever-Hall locking (PDH)
- Spectrum Broadening

### Options

- 850 nm and 1060 nm versions
- Space grade version

### Related Equipments

- RF amplifiers
- NIR-MX950-LN intensity modulators
- Reference transmitter Modbox-VNA
- 30ps optical pulse Modbox-PG

### NIR-MPX950-LN-0.1 series Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	850	900	950	nm
Usable electro-optical bandwidth	-	300	-	MHz
$V_{\pi}$ RF @50 kHz	-	2.2	-	V
Insertion loss	-	3.5	-	dB

### NIR-MPX950-LN-05 series Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	850	900	950	nm
Usable electro-optical bandwidth	-	10	-	MHz
$V_{\pi}$ RF @50 kHz	-	3.5	-	V
Insertion loss	-	3.5	-	dB

### NIR-MPX950-LN-10 series Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	850	900	950	nm
Usable electro-optical bandwidth	-	16	-	MHz
$V_{\pi}$ RF @50 kHz	-	4.5	-	V
Insertion loss	-	3.5	-	dB

### NIR-MPX950-LN-20 series Performance Highlights

Parameter	Min	Typ	Max	Unit
Operating wavelength	850	900	950	nm
Usable electro-optical bandwidth	-	20	-	MHz
$V_{\pi}$ RF @50 kHz	-	4.5	-	V
Insertion loss	-	3.5	-	dB

**NIR-MPX950-LN-0.1**

300 MHz Phase Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical (EO) bandwidth	$S_{21}$	-	100	150	-	MHz
Usable EO bandwidth	$t_r / t_f$	-		300	-	MHz
Vπ RF @50 kHz	$V\pi_{RF \text{ 50 kHz}}$	-	-	2.2	3.2	V
RF input impedance	$Z_{in-RF}$	-	-	10 000	-	Ω

**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Wavelength	-	-		Proton exchange		
Operating wavelength	$\lambda$	-	850	900	950	nm
Insertion loss	IL	Without optical connectors*	-	3.5	5.5	dB
Optical return loss	ORL	-	-40	-45	-	dB

All specifications given at 25°C, 944 nm, unless differently specified.

(\* Consider an extra-loss up to 0.6 dB for each FC/APC optical connector)

**Absolute Maximum Ratings**

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Parameter	Symbol	Min	Max	Unit
Modulation voltage range	$EV_{in}$	-20	+20	V
Optical input power (CW mode)	$OP_{in}$	-	14	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

**NIR-MPX950-LN-05**

10 GHz Phase Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical (EO) bandwidth	$S_{21}$	RF electrodes, from 2 GHz	5	-	-	GHz
Usable electro-optical bandwidth	$S_{21}$	RF electrodes, from 2 GHz	-	10	-	GHz
Ripple $S_{21}$	$\Delta S_{21}$	-	-	0.5	1	dB
Electrical return loss	$S_{11}$	-	-	-12	-10	dB
Vπ RF @50 kHz	$V\pi_{RF \text{ 50 kHz}}$	-	-	3.5	4.5	V
RF input impedance	$Z_{in-RF}$	-	-	50	-	Ω

**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Wavelength	-	-		Proton exchange		
Operating wavelength	$\lambda$	-	850	900	950	nm
Insertion loss	IL	Without optical connectors*	-	3.5	5.5	dB
Optical return loss	ORL	-	-40	-45	-	dB

All specifications given at 25°C, 944 nm, unless differently specified.

(\* Consider an extra-loss up to 0.6 dB for each FC/APC optical connector)

**Absolute Maximum Ratings**

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Parameter	Symbol	Min	Max	Unit
RF input power (CW mode)	$EV_{in}$	-	+28	dBm
Optical input power (CW mode)	$OP_{in}$	-	14	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

**NIR-MPX950-LN-10**

## 16 GHz Phase Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical (EO) bandwidth	S <sub>21</sub>	RF electrodes, from 2 GHz	10	12	-	GHz
Usable electro-optical bandwidth	S <sub>21</sub>	RF electrodes, from 2 GHz	-	16	-	GHz
Ripple S <sub>21</sub>	ΔS <sub>21</sub>	-	-	0.5	1	dB
Electrical return loss	S <sub>11</sub>	-	-	-12	-10	dB
Vπ RF @50 kHz	Vπ <sub>RF 50 kHz</sub>	-	-	4.5	5.5	V
RF input impedance	Z <sub>in-RF</sub>	-	-	50	-	Ω

**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Wavelength	-	-		Proton exchange		
Operating wavelength	λ	-	850	900	950	nm
Insertion loss	IL	Without optical connectors*	-	3.5	5.5	dB
Optical return loss	ORL	-	-40	-45	-	dB

All specifications given at 25°C, 944 nm, unless differently specified.

(\*) Consider an extra-loss up to 0.6 dB for each FC/APC optical connector

**Absolute Maximum Ratings**

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Parameter	Symbol	Min	Max	Unit
RF input power (CW mode)	EV <sub>in</sub>	-	+28	dBm
Optical input power (CW mode)	OP <sub>in</sub>	-	14	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

**NIR-MPX950-LN-20**

## 20 GHz Phase Modulator

**Electrical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Electro-optical (EO) bandwidth	S <sub>21</sub>	RF electrodes, from 2 GHz	16	20	-	GHz
Ripple S <sub>21</sub>	ΔS <sub>21</sub>	-	-	0.5	1	dB
Electrical return loss	S <sub>11</sub>	-	-	-12	-10	dB
Vπ RF @50 kHz	V <sub>π</sub> <sub>RF 50 kHz</sub>	-	-	4.5	5.5	V
RF input impedance	Z <sub>in-RF</sub>	-	-	50	-	Ω

**Optical Characteristics**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Crystal	-	-		Lithium Niobate X-Cut Y-Prop		
Wavelength	-	-		Proton exchange		
Operating wavelength	λ	-	850	900	950	nm
Insertion loss	IL	Without optical connectors*	-	3.5	5.5	dB
Optical return loss	ORL	-	-40	-45	-	dB

All specifications given at 25°C, 944 nm, unless differently specified.

(\*) Consider an extra-loss up to 0.6 dB for each FC/APC optical connector

**Absolute Maximum Ratings**

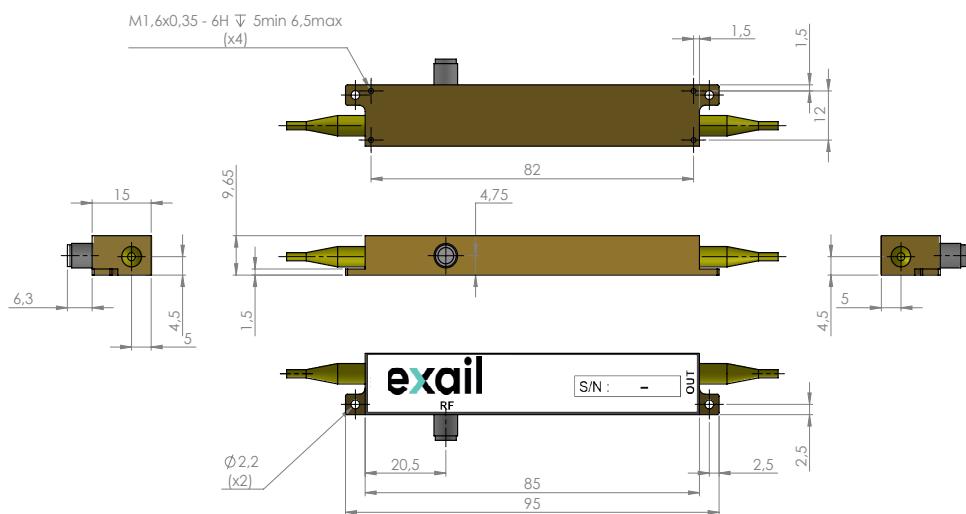
Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. These are absolute stress ratings only. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of the data sheet. Exposure to absolute maximum ratings for extended periods can adversely affect device reliability.

Parameter	Symbol	Min	Max	Unit
RF input power (CW mode)	EV <sub>in</sub>	-	+28	dBm
Optical input power (CW mode)	OP <sub>in</sub>	-	14	dBm
Operating temperature	OT	0	+70	°C
Storage temperature	ST	-40	+85	°C

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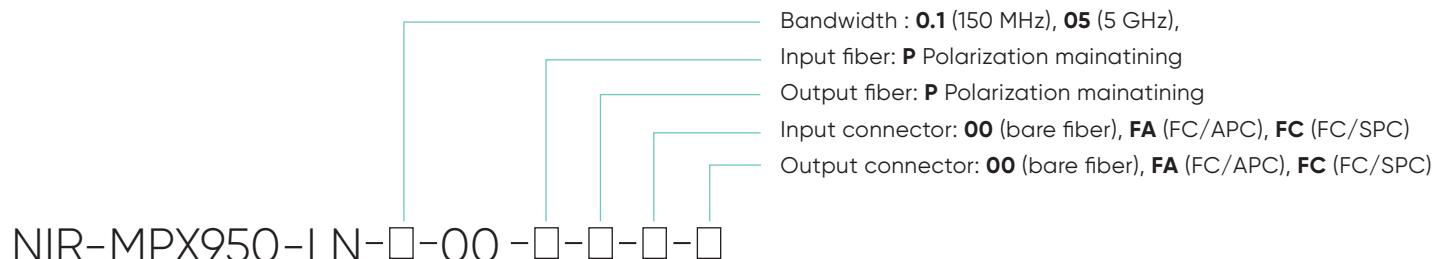
## Mechanical Diagram and Pinout

All measurements in mm



Port	Function	Note
IN	Optical input port	Polarization maintaining fiber Corning PM 98-U25D Length: 1.5 meter, buffer diameter: 900 µm
OUT	Optical output port	Polarization maintaining fiber Corning PM 98-U25D Length: 1.5 meter, buffer diameter: 900 µm
RF	RF input port	Female K

## Ordering information



## About us

Exail Photonics produces specialty optical fibers and Bragg gratings based fiber optics components and provides optical modulation solutions based on the company lithium niobate ( $\text{LiNbO}_3$ ) modulators and RF electronic modules.

Exail Photonics serves a wide range of industries: sensing and instruments, defense, telecommunications, space and fiber lasers as well as research laboratories all over the world.

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